

# Metastable Solvent Epitaxy による SiC の結晶成長シミュレーション

## Simulations on Metastable Solvent Epitaxy of SiC

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We report a method, named metastable solvent epitaxy, which enables the epitaxial growth of SiC from liquid, and whose configuration is very similar with the well-known ‘traveling solvent method’ but without temperature gradient. The driving force of solvent traveling is the chemical potential difference between 3C and 4H SiC, and is interpreted by the stable and metastable double phase diagram.